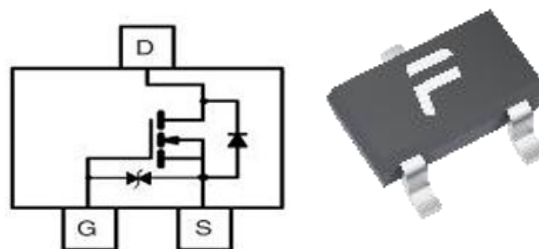


**SOT-523 20V N Channel Enhancement ESD Protection 沟道增强型带静电保护
MOS Field Effect Transistor 场效应管**



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 10	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	0.6	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	3.3	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	150	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	887	$^\circ C/W$
ESD Protected Up to 人体模式静电保护范围	ESD(HBM)	2.0	kV
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ **Device Marking 产品字标**

FS3134KE=A

Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	20	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	0.3	—	1	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =16V)	I _{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流(V _{GS} =±8V, V _{DS} =0V)	I _{GSS}	—	—	±10	μA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =0.5A, V _{GS} =4.5V) (I _D =0.2A, V _{GS} =2.5V) (I _D =0.1A, V _{GS} =1.8V)	R _{DS(ON)}	—	250 350 650	400 600 800	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} =0.15A, V _{GS} =0V)	V _{SD}	—	—	1.2	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{ISS}	—	33	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{OSS}	—	20	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{RSS}	—	10	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _g	—	0.8	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _{gs}	—	0.3	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _{gd}	—	0.15	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _{d(on)}	—	4	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _r	—	18.8	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _{d(off)}	—	10	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _f	—	23	—	ns

■ Typical Characteristic Curve 典型特性曲线

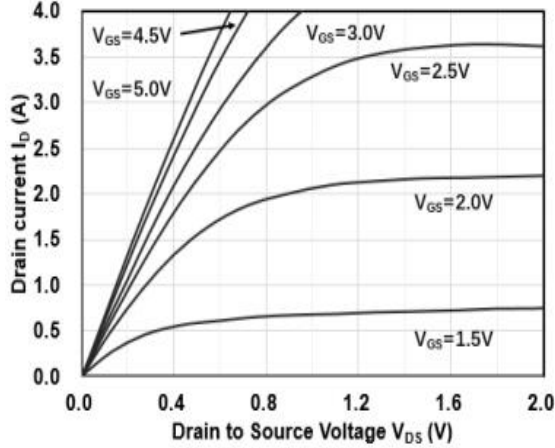


Figure 1: Output Characteristics

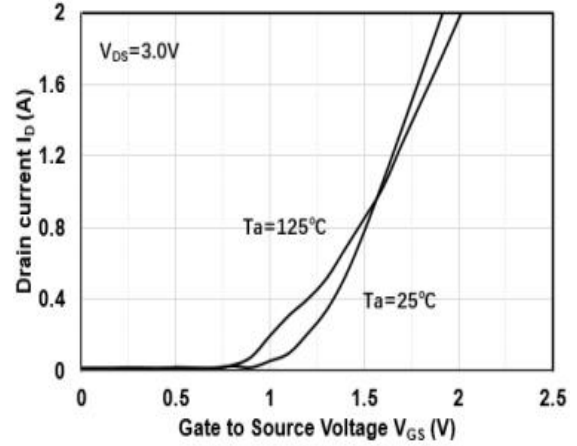


Figure 2: Transfer Characteristics

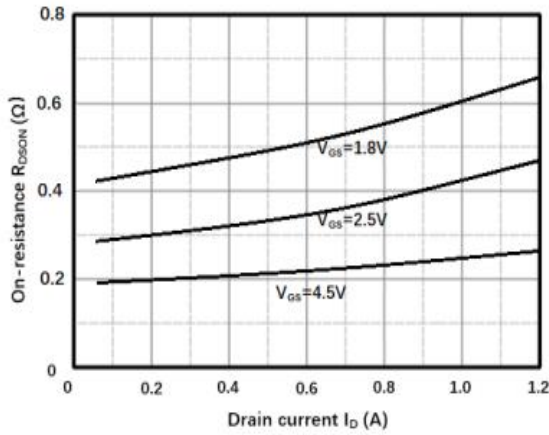


Figure 3: On-Resistance vs. Drain Current

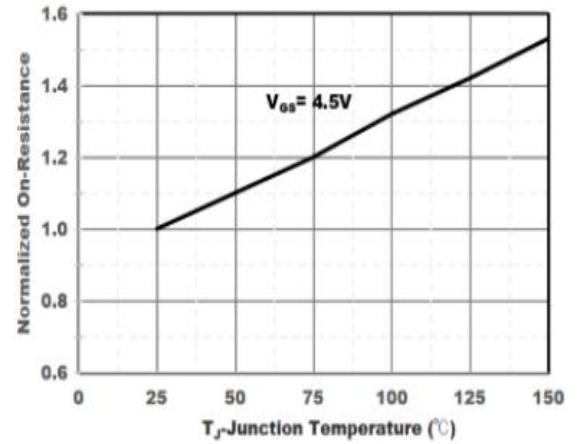


Figure 4: On-Resistance vs. Temperature

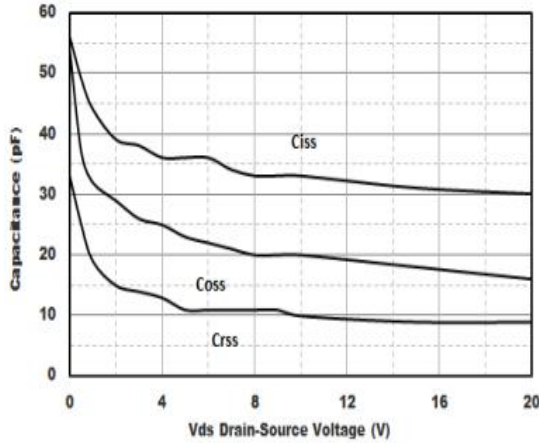


Figure 5: Capacitance Characteristics

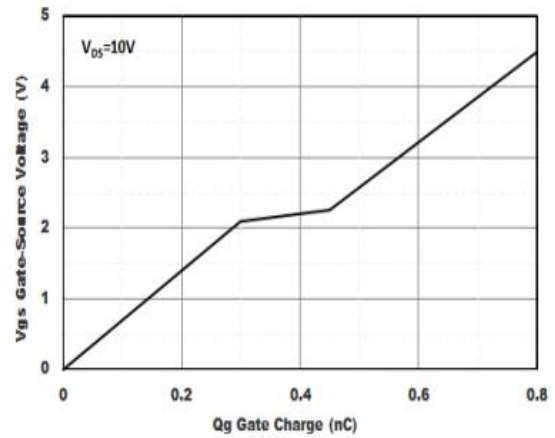


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

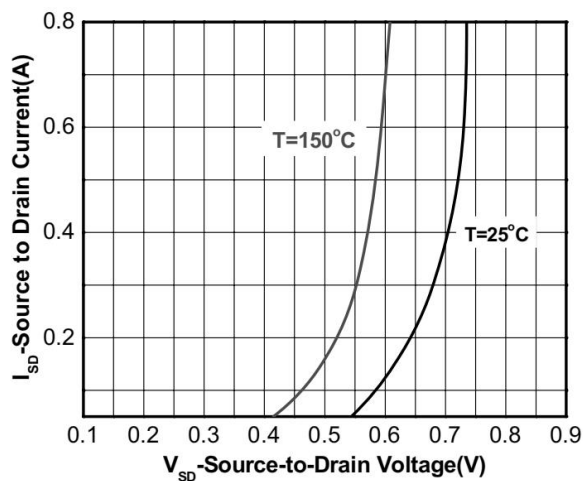


Figure 7: Diode Characteristics

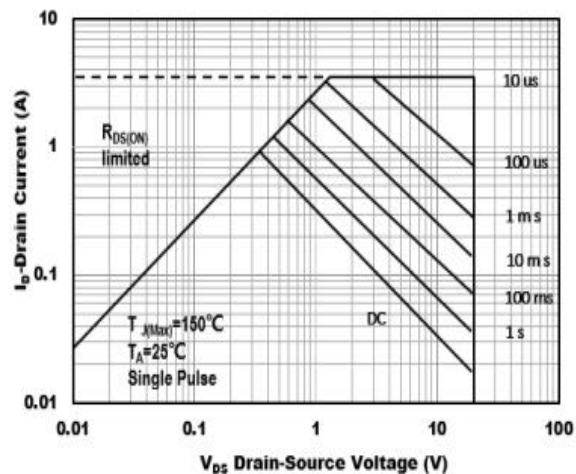


Figure 8: Safe Operating Area

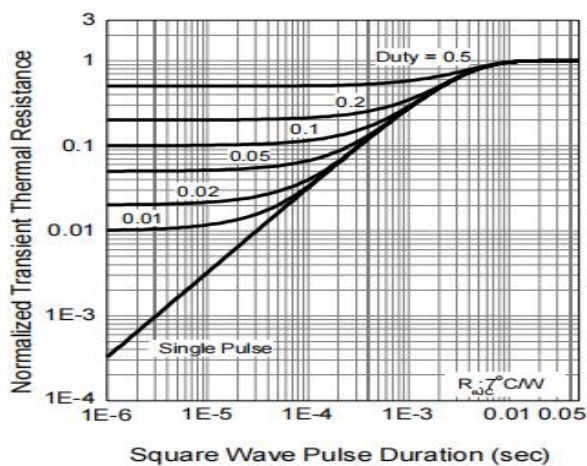
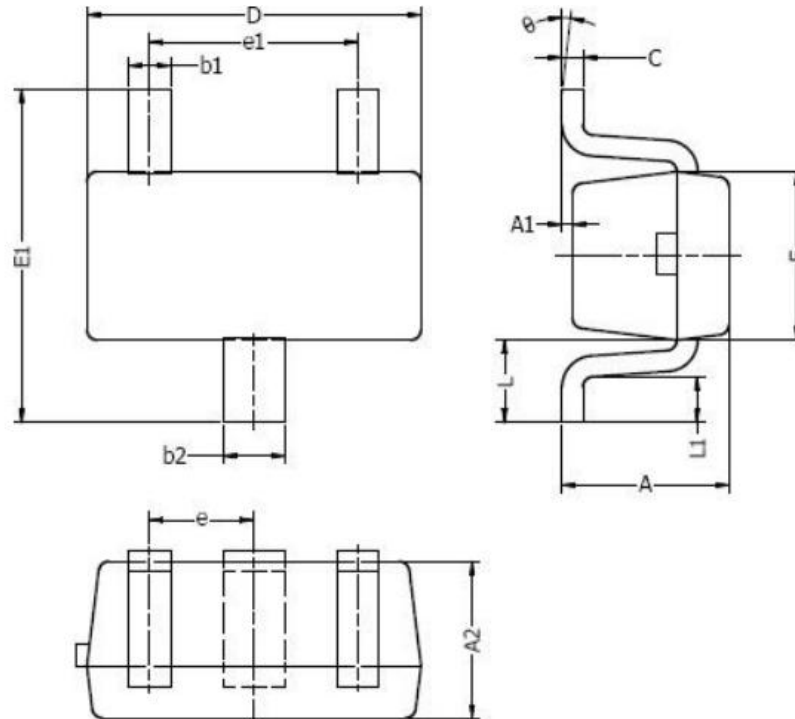


Figure 9: Transient Thermal Response Curve

■ Dimension 外形封装尺寸



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°